# **The Computer Memory**

Chapter 6 forms the first of a two-chapter sequence on computer memory.

Topics for this chapter include.

- 1. A functional description of primary computer memory, sometimes called by the obsolescent term "core memory".
- 2. A description of the memory bus, including asynchronous and the more modern synchronous busses.
- 3. Memory registers and memory timings.
- 4. Registers and flip–flops.
- 5. The basic memory unit.
- 6. The physical view of memory. How commercial memory is organized.
- 7. Managing the address: column address, row address, and strobes.
- 8. The evolution of modern memory chips.

# **The Memory Component**

The memory stores the instructions and data for an executing program.

Memory is characterized by the smallest addressable unit:Byte addressablethe smallest unit is an 8-bit byte.Word addressablethe smallest unit is a word, usually 16 or 32 bits in length.

Most modern computers are byte addressable, facilitating access to character data.

Logically, computer memory should be considered as an array. The index into this array is called the **address** or **"memory address"**.

A logical view of such a byte addressable memory might be written in code as:

Const	MemSize =		
byte	Memory[MemSize]	// Indexed 0	(MemSize - 1)

The CPU has two registers dedicated to handling memory.

- The MAR (Memory Address Register) holds the address being accessed.
- The **MBR** (Memory Buffer Register) holds the data being written to the memory or being read from the memory. This is sometimes called the Memory Data Register.

# **Requirements for a Memory Device**

- Random access by address, similar to use of an array. Byte addressable memory can be considered as an array of bytes. byte memory [N] // Address ranges from 0 to (N – 1)
- 2. Binary memory devices require two reliable stable states.
- 3. The transitions between the two stable states must occur quickly.
- 4. The transitions between the two stable states must not occur spontaneously, but only in response to the proper control signals.
- 5. Each memory device must be physically small, so that a large number may be placed on a single memory chip.
- 6. Each memory device must be relatively inexpensive to fabricate.

#### **Varieties of Random Access Memory**

There are two types of RAM

- 1. RAM read/write memory
- 2. ROM read–only memory.

The double use of the term "RAM" is just accepted. Would you say "RWM"?

#### Types of ROM

- 1. "Plain ROM" the contents of the memory are set at manufacture and cannot be changed without destroying the chip.
- 2. PROM the contents of the chip are set by a special device called a "PROM Programmer". Once programmed the contents are fixed.
- 3. EPROM same as a PROM, but that the contents can be erased and reprogrammed by the PROM Programmer.

# **Memory Control Signals**

Read / Write Memory must do three actions:

- READ copy contents of an addressed word into the MBR
- WRITE copy contents of the MBR into an addressed word
- NOTHING the memory is expected to retain the contents written into it until those contents have been rewritten.

One set of control signals **Select#** – the memory unit is selected.

**R/W#** if 0 the CPU writes to memory, if 1 the CPU reads from memory.

Select#	<b>R/W</b> #	Action
0	0	CPU writes data to the memory.
0	1	CPU reads data from the memory.
1	0	Memory contents are not changed.
1	1	Memory contents are not changed.

A ROM has only one control signal: Select.

If Select = 1 for a ROM, the CPU reads data from the addressed memory slot.

# **Memory Timings**

#### **Memory Access Time**

Defined in terms of reading from memory. It is the time between the address becoming stable in the MAR and the data becoming available in the MBR.

# READ SEQUENCE



#### **Memory Cycle Time**

Less used, this is defined as the minimum time between two independent memory accesses.

# **The Memory Bus**

The memory bus is a dedicated point—to—point bus between the CPU and computer memory. The bus has the following lines.

1. Address lines used to select the memory chip containing the addressed memory word and to address that word within the memory.

These are used to generate the signal **Select**#, sent to each memory chip.

- 2. **Data lines** used to transfer data between the CPU and memory.
- 3. **Bus Clock** is present on a synchronous bus to coordinate transfers.
- 4. **Control lines** such as the R/W# control signal mentioned above.

Some **control lines**, called strobe lines, assert the validity of data on associated lines.

When **RAS** (**R**ow Address Strobe) is asserted, the row address on the memory address line is certified to be a valid address.

#### **A Synchronous Bus Timing Diagram**



This is a bus read. The sequence: the address becomes valid, RD# is asserted, and later the data become valid.

# **An Asynchronous Bus Timing Diagram**

Here, the importance is the interplay of the **Master Synchronization (MSYN#)** and **Slave Synchronization (SSYN#)** signals.



The sequence: 1. The address becomes valid; **MREQ**# and **RD**# are asserted low.

- 2. **MSYN#** is asserted low, causing the memory to react.
- 3. Data become valid and **SSYN#** is asserted low.
- 4. When **SSYN**# goes high, the data are no longer valid.

# **Sequential Circuits**

- **Sequential circuits** are those with memory, also called "feedback". In this, they differ from **combinational circuits**, which have no memory.
- The stable output of a combinational circuit does not depend on the order in which its inputs are changed. The stable output of a sequential circuit usually does depend on the order in which the inputs are changed.

Sequential circuits can be used as memory elements; binary values can be stored in them. The binary value stored in a circuit element is often called that element's **state**.

All sequential circuits depend on a phenomenon called **gate delay**. This reflects the fact that the output of any logic gate (implementing a Boolean function) does not change immediately when the input changes, but only some time later.

The gate delay for modern circuits is typically a few nanoseconds.



# **Synchronous Sequential Circuits**

#### We usually focus on **clocked sequential circuits**, also called **synchronous sequential circuits**.

As the name **"synchronous"** implies, these circuits respond to a system clock, which is used to synchronize the state changes of the various sequential circuits.

One textbook claims that "synchronous sequential circuits use clocks to order events." A better claim might be that the clock is used to coordinate events. Events that should happen at the same time do; events that should happen later do happen later.

The **system clock** is a circuit that emits a sequence of regular pulses with a fixed and reliable pulse rate. If you have an electronic watch (who doesn't?), what you have is a small electronic circuit emitting pulses and a counter circuit to count them.

Clock frequencies are measured in

kilohertz	thousands of ticks per second
megahertz	millions of ticks per second
gigahertz	billions of ticks per second.

One can design **asynchronous sequential circuits**, which are not controlled by a s ystem clock. They present significant design challenges related to timing issues.

## **Views of the System Clock**

There are a number of ways to view the system clock. In general, the view depends on the detail that we need in discussing the problem. The logical view is shown in the next figure, which illustrates some of the terms commonly used for a clock.



The clock is typical of a periodic function. There is a period  $\tau$  for which

 $\mathbf{f}(t) = \mathbf{f}(t + \tau)$ 

This clock is **asymmetric**. It is often the case that the clock is **symmetric**, where the time spent at the high level is the same as that at the low level. Your instructor often draws the clock as asymmetric, just to show that such a design is allowed.

**NOTATION:** We always call the present clock tick "t" and the next one "t + 1", even if it occurs only two nanoseconds later.



**Views of the System Clock** 

The top view is the "real physical view". It is seldom used.

The middle view reflects the fact that voltage levels do not change instantaneously.

We use this view when considering system busses.

### **Clock Period and Frequency**

If the clock period is denoted by  $\tau$ , then the frequency (by definition) is  $f = 1 / \tau$ .

For example, if  $\tau = 2.0$  nanoseconds, also written as  $\tau = 2.0 \cdot 10^{-9}$  seconds, then  $f = 1 / (2.0 \cdot 10^{-9} \text{ seconds}) = 0.50 \cdot 10^{9} \text{ seconds}^{-1}$  or 500 megahertz.

If f = 2.5 Gigahertz, also written as  $2.5 \cdot 10^9$  seconds<sup>-1</sup>, then  $\tau = 1.0 / (2.5 \cdot 10^9 \text{ seconds}^{-1}) = 0.4 \cdot 10^{-9} \text{ seconds} = 0.4$  nanosecond.

Memory bus clock frequencies are in the range 125 to 1333 MHz (1.33 GHz).

CPU clock frequencies generally are in the 2.0 to 6.0 GHz range, with 2.0 to 3.5 GHz being far the most common.

The IBM z196 Enterprise Server contains 96 processors, each running at 5.2 GHz. Each processor is water cooled.

# **Latches and Flip–Flops: First Definition**

We consider a latch or a flip–flop as a device that stores a **single binary value**.

Flip–flops and clocked latches are devices that accept input at fixed times dictated by the system clock. For this reason they are called **"synchronous sequential circuits"**.

Denote the present time by the symbol  $\mathbf{t}$ . Denote the clock period by  $\tau$ .

Rather than directly discussing the clock period, we merely say that

the current time is **t** 

after the next clock tick the time is (t + 1)

The present state of the device is often called Q(t)The next state of the device is often called Q(t + 1)

The sequence: the present state is Q(t), the clock "ticks", the state is now Q(t + 1)

AGAIN: We call the next state Q(t + 1), even if the transition from Q(t) to Q(t + 1) takes only a few nanoseconds. We are counting the actual number of clock ticks, not the amount of time they take.

# Latches and Flip–Flops: When Triggered

Clocked latches accept input when the system clock is at logic high.



Flip–flops accept input on either the rising edge of the system clock.



# **Describing Flip–Flops**

A flip–flop is a **"bit bucket"**; it holds a single binary bit. A flip–flop is characterized by its current state: Q(**t**).

We want a way to describe the operation of the flip–flops. How do these devices respond to the input? We use tables to describe the operation.

Characteristic tables:	Given $Q(t)$ , the present state of the flip-flop, and	
	the input, what will $Q(t + 1)$ , the next state of the flip-flop, be?	

Excitation tables:	Given $Q(\mathbf{t})$ , the present state of the flip-flop, and
	Q(t + 1), the desired next state of the flip-flop,
	what input is required to achieve that change.

### **SR Flip–Flop**

We now adopt a functional view. How does the next state depend on the present state and input. A flip–flop is a "bit holder".

Here is the diagram for the SR flip–flop.



Here again is the state table for the SR flip–flop.

S	R	Q(t + 1)
0	0	Q(T)
0	1	0
1	0	1
1	1	ERROR

Note that setting both S = 1 and R = 1 causes the flip-flop to enter a logically inconsistent state, followed by an undeterministic, almost random, state. For this reason, we label the output for S = 1 and R = 1 as an error.

# JK Flip–Flop

A JK flip–flop generalizes the SR to allow for both inputs to be 1.



Here is the characteristic table for a JK flip–flop.

J	K	Q(t + 1)
0	0	Q(t)
0	1	0
1	0	1
1	1	$\overline{\mathbf{Q}(t)}$

Note that the flip-flop can generate all four possible functions of a single variable: the two constants 0 and 1 the variables Q and  $\overline{Q}$ .

# The D Flip–Flop

The D flip–flop specializes either the SR or JK to store a single bit. It is very useful for interfacing the CPU to external devices, where the CPU sends a brief pulse to set the value in the device and it remains set until the next CPU signal.



The characteristic table for the D flip-flop is so simple that it is expressed better as the equation Q(t + 1) = D. Here is the table.

D	Q(t + 1)
0	0
1	1

The D flip–flop plays a large part in computer memory.

Some memory types are just large collections of D flip-flops.

The other types are not fabricated from flip-flops, but act as if they were.

### **The T Flip–Flop**

The "toggle" flip–flop allows one to change the value stored. It is often used in circuits in which the value of the bit changes between 0 and 1, as in a modulo–4 counter in which the low–order bit goes 0, 1, 0, 1, 0, 1, etc.



The characteristic table for the D flip–flop is so simple that it is expressed better as the equation  $Q(t + 1) = Q(t) \oplus T$ . Here is the table.

Т	Q(t + 1)
0	Q(t)
1	$\overline{\mathbf{Q}(t)}$

# **Memory Mapped Input / Output**

Though not a memory issue, we now address the idea of memory mapped input and output. In this scheme, we take part of the address space that would otherwise be allocated to memory and allocate it to I/O devices.

The PDP–11 is a good example of a memory mapped device. It was a byte addressable device, meaning that each byte had a unique address.

The old PDP–11/20 supported a 16–bit address space. This supported addresses in the range 0 through 65,535 or 0 through 0177777 in octal.

Addresses 0 though 61,439 were reserved for physical memory. In octal these addresses are given by 0 through 167,777.

Addresses 61,440 through 65,535 (octal 170,000 through 177,777) were reserved for registers associated with Input/Output devices.

Examples:	CR11 Card Reader	177,160	Control & Status Register
		177,162	Data buffer 1
		177,164	Data buffer 2

Reading from address 0177162 would access the card reader data buffer.

#### **The Linear View of Memory**

Memory may be viewed as a linear array, for example a byte-addressable memory

byte memory [N] ; // Addresses 0 .. (N - 1)



This is a perfectly good logical view, it just does not correspond to reality.

#### **Memory Chip Organization**

Consider a 4 Megabit memory chip, in which each bit is directly addressable. Recall that  $4M = 2^{22} = 2^{11} \bullet 2^{11}$ , and that  $2^{11} = 2,048$ .

- The linear view of memory, on the previous slide, calls for a 22–to–2<sup>22</sup> decoder, also called a 22–to–4,194,304 decoder. This is not feasible.
- If we organize the memory as a two–dimensional grid of bits, then the design calls for two 11–to–2048 decoders. This is still a stretch.



#### **Managing Pin-Outs**

Consider now the two-dimensional memory mentioned above. What pins are needed?



Separate row and column addresses require two cycles to specify the address.

#### **Four–Megabyte Memory**

Do we have a single four-megabyte chip or eight four-megabit memory chips?

One common solution is to have bit-oriented chips. This facilitates the two-dimensional addressing discussed above.



For applications in which data integrity is especially important, one might add a ninth chip to hold the parity bit. This reflects the experience that faults, when they occur, will be localized in one chip.

Parity provides a mechanism to detect, but not correct, single bit errors.

Correction of single bit errors requires twelve memory chips. This scheme will also detect all two-bit errors.

### **Memory Interleaving**

Suppose a 64MB memory made up of the 4Mb chips discussed above. We now ignore parity memory, for convenience and also because it is rarely needed.

We organize the memory into 4MB banks, each having eight of the 4Mb chips. The figure in the slide above shows such a bank.

The memory thus has 16 banks, each of 4MB.

$16 = 2^4$	4 bits to select the bank
$4M = 2^{22}$	22 bits address to each chip

Not surprisingly,  $64M = 2^{26}$ .

Low–Order Interleaving

Bits	25-4	3-0
Use	Address to the chip	Bank Select

High–Order Interleaving (Memory Banking)

Bits	25 - 22	21-0
Use	Bank Select	Address to the chip

Most designs use low order interleaving to reduce effective memory access times.

#### **Faster Memory Chips**

We can use the "2 dimensional" array approach, discussed earlier, to create a faster memory. This is done by adding a SRAM (Static RAM) buffer onto the chip. Consider the 4Mb (four megabit) chip discussed earlier, now with a 2Kb SRAM buffer.



In a modern scenario for reading the chip, a Row Address is passed to the chip, followed by a number of column addresses. When the row address is received, the entire row is copied into the SRAM buffer. Subsequent column reads come from that buffer.

# **Memory Technologies: SRAM and DRAM**

One major classification of computer memory is into two technologies

SRAM	Static Random Access Memory
DRAM	Dynamic Random Access Memory (and its variants)

SRAM is called static because it will keep its contents as long as it is powered.

DRAM is called **dynamic** because it tends to lose its contents, even when powered. Special "refresh circuitry" must be provided.

Compared to DRAM, SRAM is

faster more expensive physically larger (fewer memory bits per square millimeter)

SDRAM is a Synchronous DRAM.

It is DRAM that is designed to work with a Synchronous Bus, one with a clock signal.

The memory bus clock is driven by the CPU system clock, but it is always slower.

#### **SDRAM (Synchronous DRAM)**

Synchronous Dynamic Random Access Memory

Suppose a 2 GHz system clock. It can easily generate the following memory bus clock rates: 1GHz, 500 MHz, 250MHz, 125MHz, etc. Other rates are also possible.

Consider a 2 GHz CPU with 100 MHz SDRAM. The CPU clock speed is 2 GHz = 2,000 MHz The memory bus speed is 100 MHz.

In **SDRAM**, the memory transfers take place on a timing dictated by the memory bus clock rate. This memory bus clock is always based on the system clock.

In "plain" SDRAM, the transfers all take place on the rising edge of the memory bus clock. In **DDR SDRAM** (Double Data Rate Synchronous DRAM), the transfers take place on both the rising and falling clock edges.



#### **Speed Up Access by Interleaving Memory**

We have done all we can to make the memory chips faster. How do we make the memory itself faster with the chips we have?

Suppose an 8-way low-order interleaved memory. The chip timings are:

Cycle time: 80 nanoseconds between independent memory reads

Access time 40 nanoseconds to place requested data in the MBR.

Each chip by itself has the following timing diagram.



This memory chip can be accessed once every 80 nanoseconds.

### **The Same Memory with 8–Way Interleaving**

Suppose a set of sequential read operations, beginning at address 1000. The interleaving is **low–order**.

Chip 0 has addresses 1000, 1008, 1016, etc.

Chip 1 has addresses 1001, 1009, 1017, etc.

Chip 7 has addresses 1007, 1015, 1023, etc.



Note that the accesses can be overlapped, with a net speedup of 8X.

# Latency and Bandwidth

Look again at this figure.



Each memory bank has a cycle time of 80 nanoseconds.

The first memory request takes 40 nanoseconds to complete.

The first time is called **latency**. This is the time interval between the first request and its completion.

After that, there is one result every 10 nanoseconds. As a bandwidth, this is 100 million transfers per second.

### **Fat Data Busses**

Here is another trick to speed up memory transfers.

In the above example, we assumed that the memory was byte addressable, having an 8-bit data bus between it and the CPU.

At one transfer every 10 nanoseconds, this is 100 megabytes per second.

Our simplistic analysis assumed that these transfers were directly to the CPU.

When we discuss cache memory, we shall see that the transfers are between main memory and the L2 (Level 2) cache memory – about 1 MB in size.

Suppose that the main feature of the L2 cache is an 8–byte cache line.

For now, this implies that 8 byte transfers between the L2 cache and main memory are not only easy, but also the most natural unit of transaction.

We link the L2 cache and main memory with 64 data lines, allowing 8 bytes to be moved for each memory transfer. We now have 800 megabytes/sec.

### **More on SDRAM**

"Plain" SDRAM makes a transfer every cycle of the memory bus. For a 100 MHz memory bus, we would have 100 million transfers per second.

DDR-SDRAM is Double Data Rate SDRAM

DDR–SDRAM makes two transfers for every cycle of the memory bus, one on the rising edge of the clock cycle one on the falling edge of the clock cycle.

For a 100 MHz memory bus, DDR–SDRAM would have 200 million transfers per second.

To this, we add wide memory buses. A typical value is a 64-bit width.

A 64-bit wide memory bus transfers 64 bits at a time. That is 8 bytes at a time.

Thus our sample DDR–SDRAM bus would transfer 1,600 million bytes per second.

This might be called 1.6 GB / second, although it more properly is 1.49 GB / second, as 1 GB = 1, 073, 741, 824 bytes.

### **Evolution of Modern Memory**

Here are some actual cost & performance data for memory.

Year	Cost per MB	Actual component		Speed	Туре
	in US \$	Size (KB)	Cost	nsec.	
1957	411,041,792.00	0.0098	392.00	10,000	transistors
1959	67,947,725.00	0.0098	64.80	10,000	vacuum tubes
1965	2,642,412.00	0.0098	2.52	2,000	core
1970	734,003.00	0.0098	0.70	770	core
1975	49,920.00	4	159.00	??	static RAM
1981	4,479.00	64	279.95	??	dynamic RAM
1985	300.00	2,048	599.00	??	DRAM
1990	46.00	1,024	45.50	80	SIMM
1996	5.25	8,192	42.00	70	72 pin SIMM
2001	15¢	128 MB	18.89	133 MHz	DIMM
2006	7.3¢	2,048 MB	148.99	667 MHz	DIMM DDR2
2008	1.0¢	4,096 MB	39.99	800 MHz	DIMM DDR2
2010	1.22¢	8,192 MB	99.99	1333 MHz	DIMM DDR2